

Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	650	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$	8.5
Q_g (Max.) (nC)	14	
Q_{gs} (nC)	2.7	
Q_{gd} (nC)	8.1	
Configuration	Single	

FEATURES

- Low Gate Charge Q_g Results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current



RoHS
COMPLIANT
HALOGEN
FREE
Available

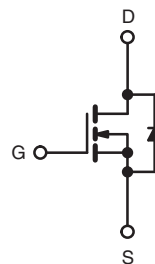
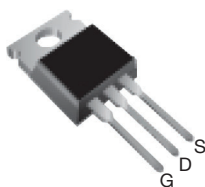
APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply
- Power Factor Correction

TYPICAL SMPS TOPOLOGIES

- Low Power Single Transistor Flyback

TO-220AB



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	650	V
Gate-Source Voltage		V_{GS}	± 30	
Continuous Drain Current	V_{GS} at 10 V	I_D	$T_C = 25\text{ }^\circ\text{C}$	1.4
			$T_C = 100\text{ }^\circ\text{C}$	0.89
Pulsed Drain Current ^a		I_{DM}	5.6	A
Linear Derating Factor			0.28	$\text{W}/^\circ\text{C}$
Single Pulse Avalanche Energy ^b		E_{AS}	93	mJ
Repetitive Avalanche Current ^a		I_{AR}	1.4	A
Repetitive Avalanche Energy ^a		E_{AR}	3.6	mJ
Maximum Power Dissipation		P_D	36	W
$T_C = 25\text{ }^\circ\text{C}$				
Peak Diode Recovery dV/dt^c		dV/dt	3.8	V/ns
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature) ^d		for 10 s	300	


Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting $T_J = 25\text{ }^\circ\text{C}$, $L = 95\text{ mH}$, $R_g = 25\text{ }\Omega$, $I_{AS} = 1.4\text{ A}$ (see fig. 12).
- $I_{SD} \leq 1.4\text{ A}$, $dI/dt \leq 180\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^\circ\text{C}$.
- 1.6 mm from case.

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	110	°C/W
Maximum Junction-to-Ambient (PCB Mount) ^a	R_{thJA}	-	50	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	3.5	

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		650	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30\text{ V}$		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$		-	-	25	μA
		$V_{DS} = 520\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$		-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 0.84\text{ A}^b$	-	8.5	-	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}, I_D = 0.84\text{ A}$		0.88	-	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V},$ $V_{DS} = 25\text{ V},$ $f = 1.0\text{ MHz},$ see fig. 5		-	229	-	pF
Output Capacitance	C_{oss}			-	32.6	-	
Reverse Transfer Capacitance	C_{rss}			-	2.4	-	
Output Capacitance	C_{oss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 1.0\text{ V}, f = 1.0\text{ MHz}$	-	320	-	pF
			$V_{DS} = 480\text{ V}, f = 1.0\text{ MHz}$	-	11.5	-	
Effective Output Capacitance	$C_{oss\text{ eff.}}$	$V_{DS} = 0\text{ V to } 480\text{ V}^c$		-	130	-	pF
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 1.4\text{ A}, V_{DS} = 400\text{ V},$ see fig. 6 and 13 ^b	-	-	14	nC
Gate-Source Charge	Q_{gs}			-	-	2.7	
Gate-Drain Charge	Q_{gd}			-	-	8.1	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 250\text{ V}, I_D = 1.4\text{ A},$ $R_g = 2.15\text{ }\Omega, R_D = 178\text{ }\Omega,$ see fig. 10 ^b		-	9.8	-	ns
Rise Time	t_r			-	14	-	
Turn-Off Delay Time	$t_{d(off)}$			-	18	-	
Fall Time	t_f			-	20	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	1.4	A
Pulsed Diode Forward Current ^a	I_{SM}			-	-	5.6	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 1.4\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	1.6	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = 1.4\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$		-	290	440	ns
Body Diode Reverse Recovery Charge	Q_{rr}			-	510	760	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.
- $C_{oss\text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

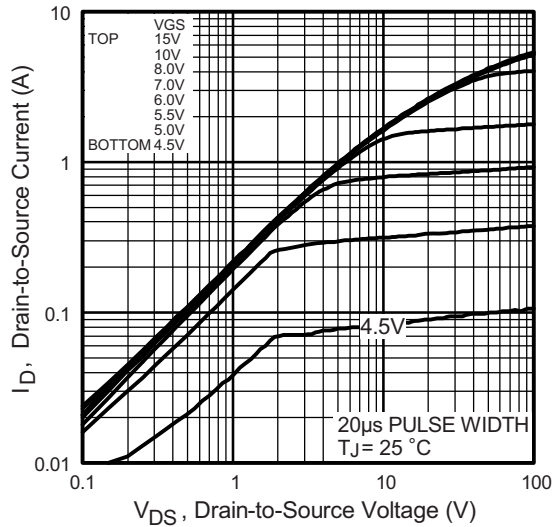


Fig. 1 - Typical Output Characteristics

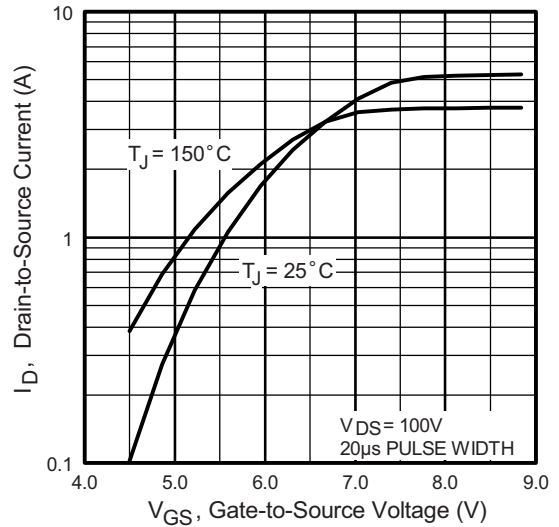


Fig. 3 - Typical Transfer Characteristics

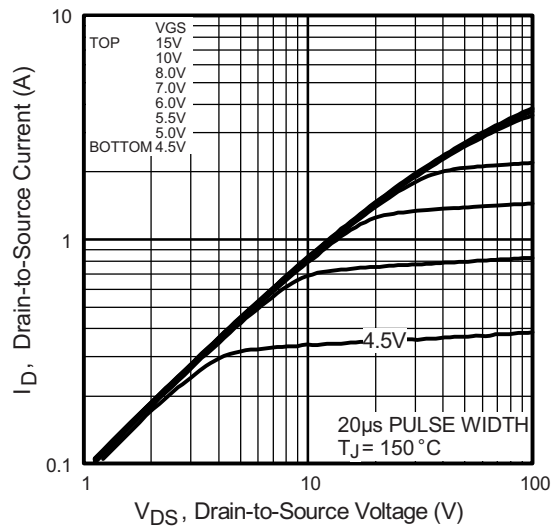


Fig. 2 - Typical Output Characteristics

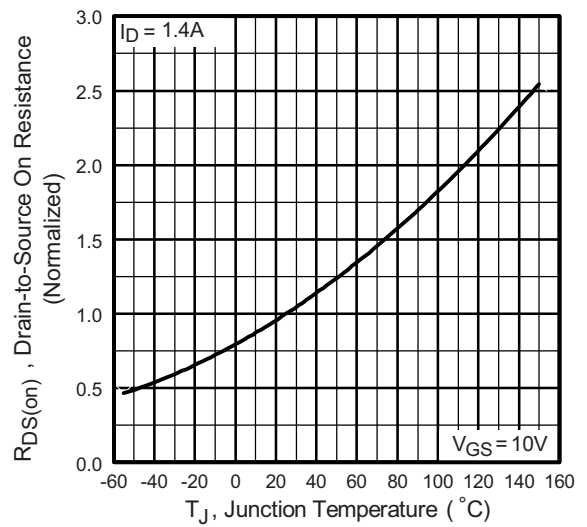


Fig. 4 - Normalized On-Resistance vs. Temperature

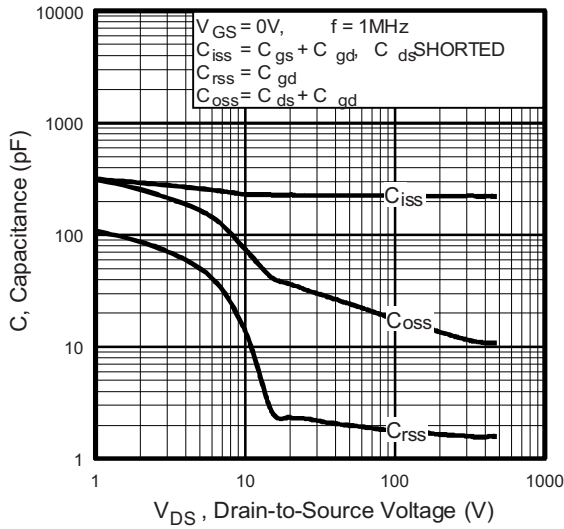


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

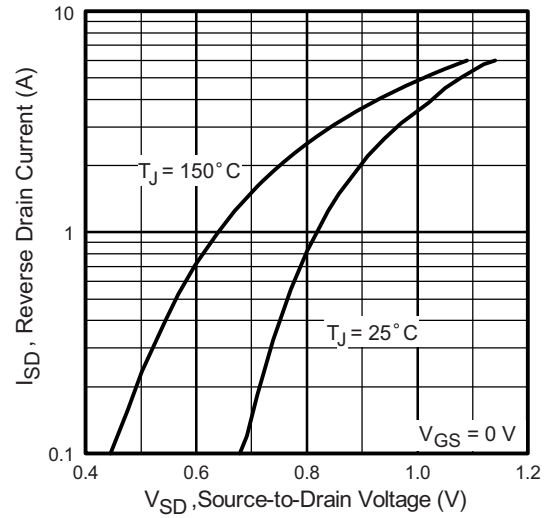


Fig. 7 - Typical Source-Drain Diode Forward Voltage

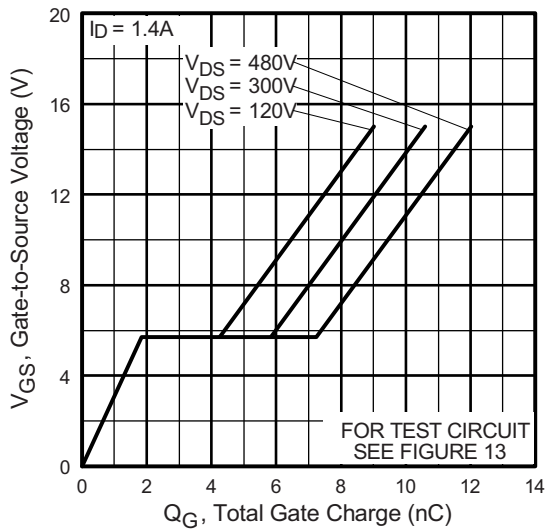


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

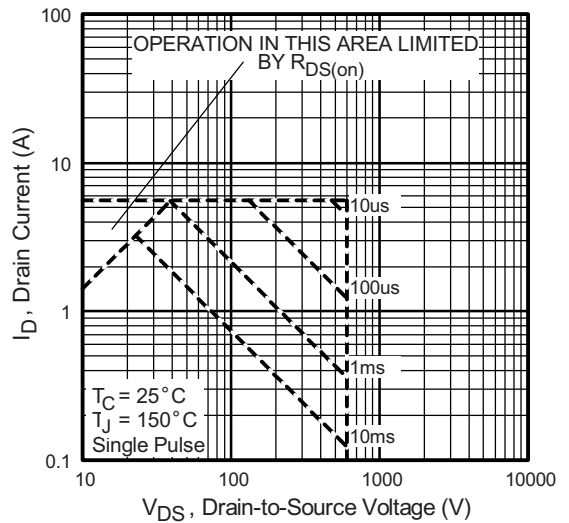


Fig. 8 - Maximum Safe Operating Area

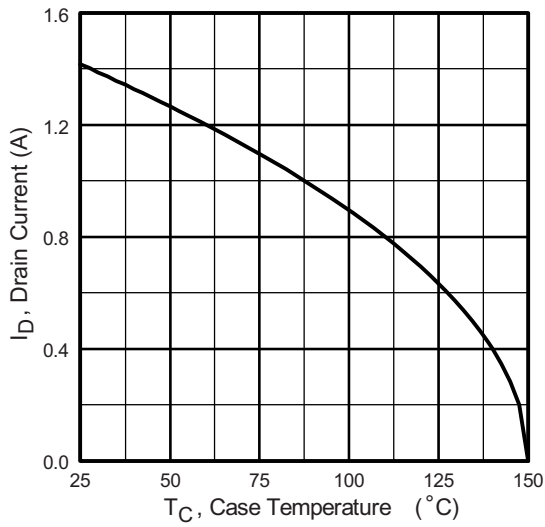


Fig. 9 - Maximum Drain Current vs. Case Temperature

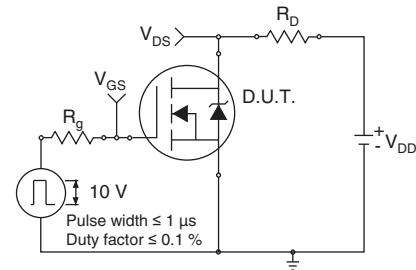


Fig. 10a - Switching Time Test Circuit

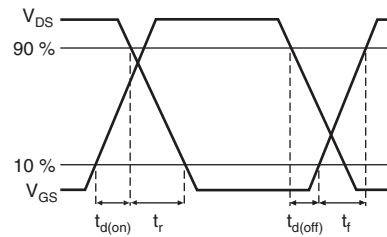


Fig. 10b - Switching Time Waveforms

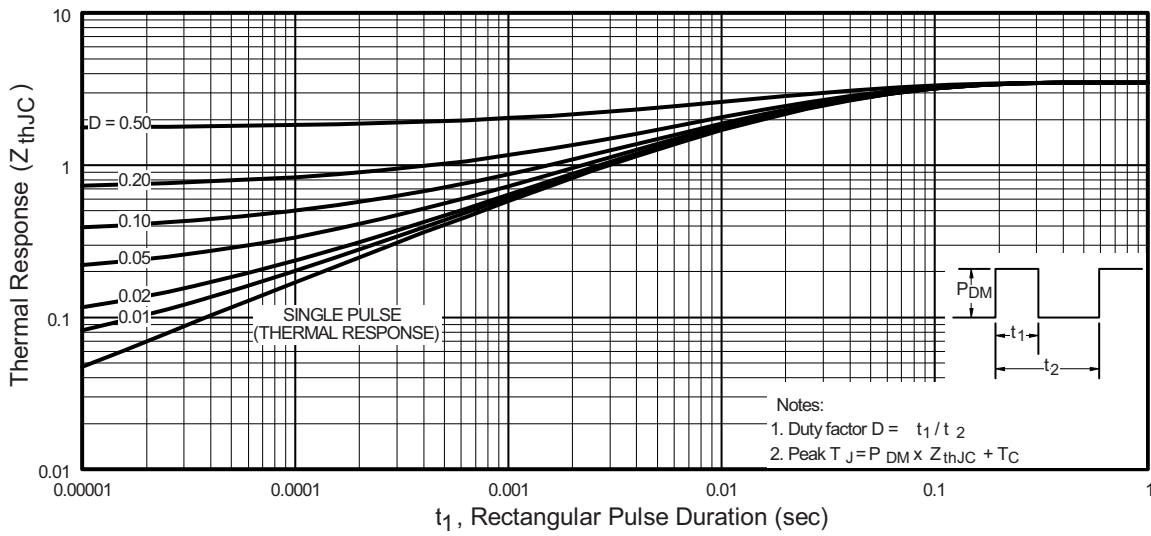


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

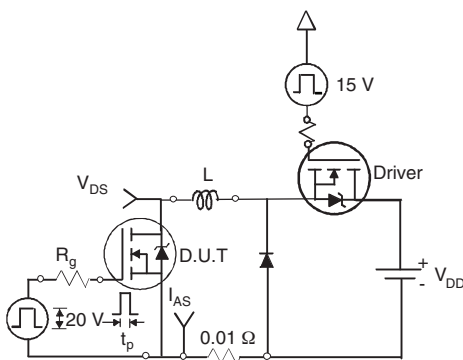


Fig. 12a - Unclamped Inductive Test Circuit

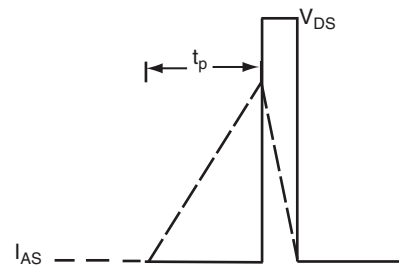


Fig. 12b - Unclamped Inductive Waveforms

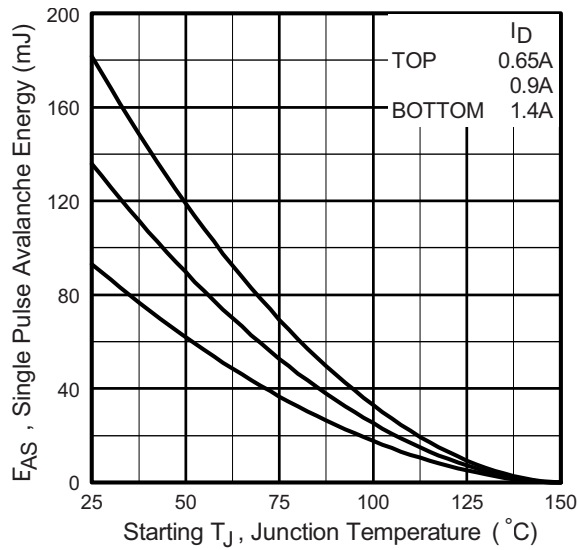


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

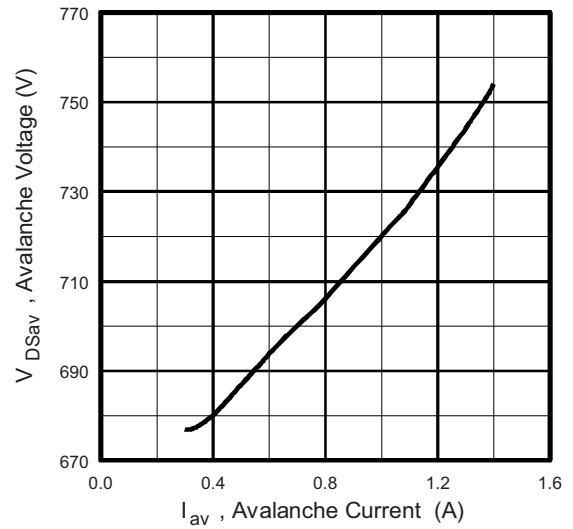


Fig. 12d - Basic Gate Charge Waveform

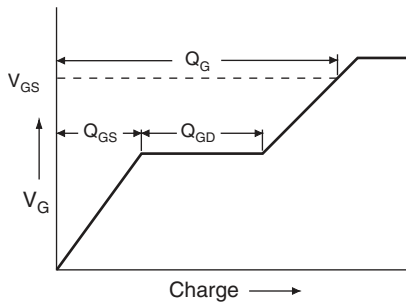


Fig. 13a - Maximum Avalanche Energy vs. Drain Current

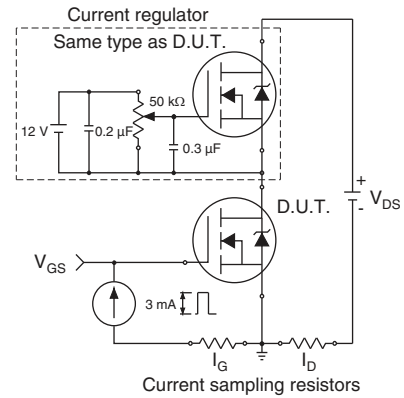
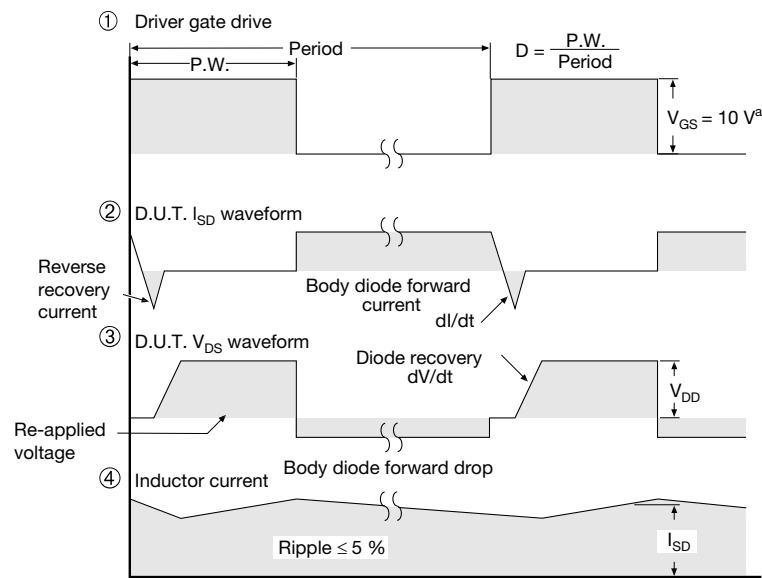
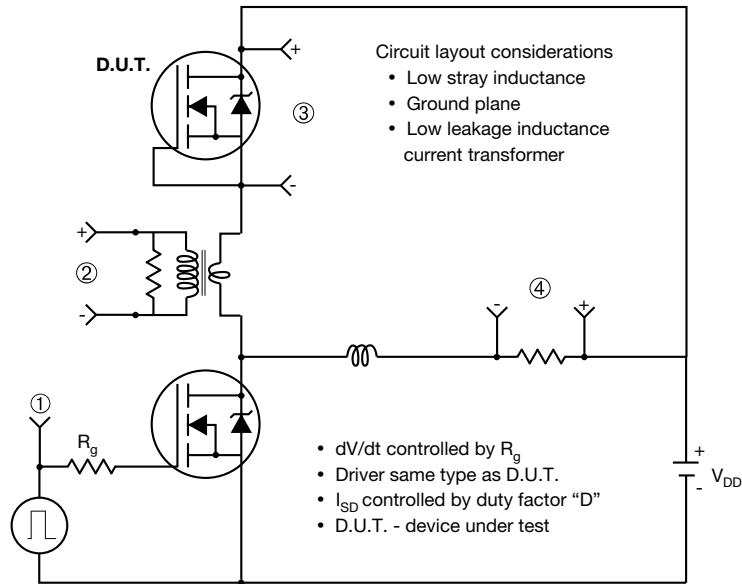


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit

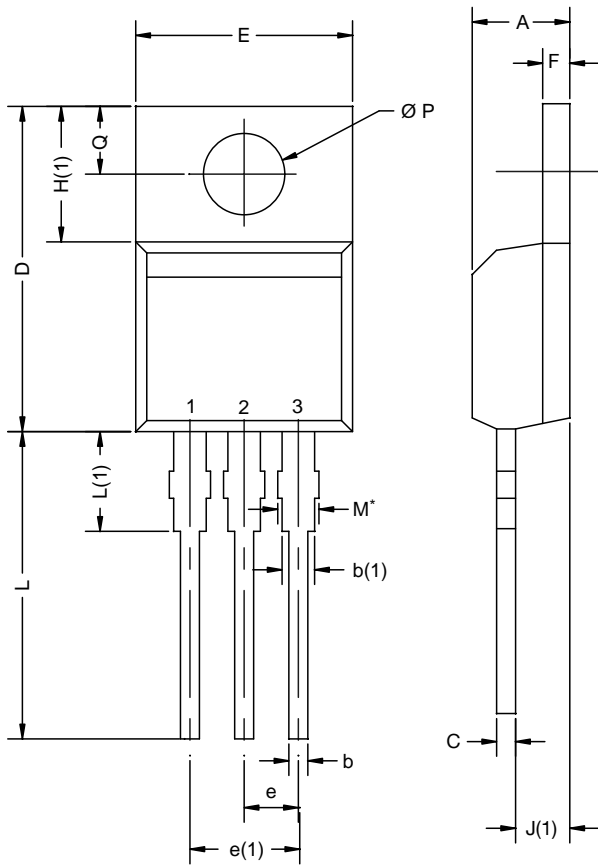


Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel

TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
$\varnothing P$	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118
ECN: X12-0208-Rev. N, 08-Oct-12 DWG: 5471				

Notes

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM

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